


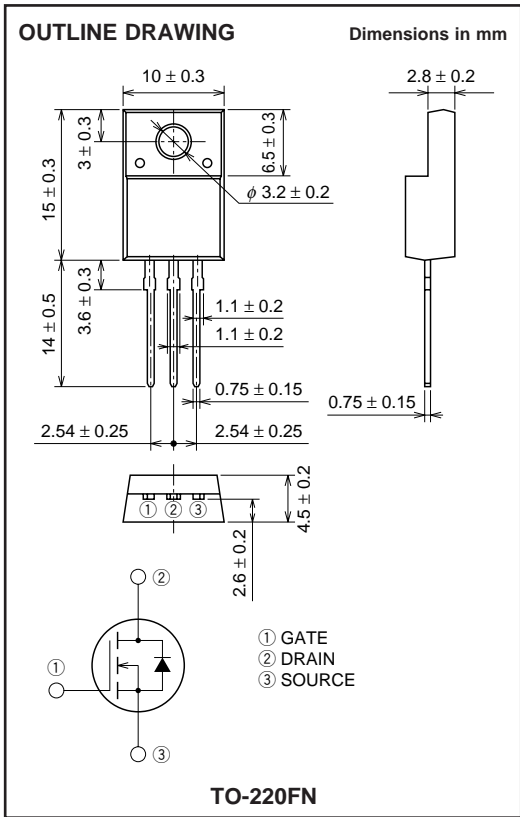
FS10KM-3

HIGH-SPEED SWITCHING USE

FS10KM-3



- 10V DRIVE
- V_{DSS} 150V
- r_{DS (ON)} (MAX) 170mΩ
- I_D 10A
- Integrated Fast Recovery Diode (TYP.) 100ns
- V_{iso} 2000V



APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

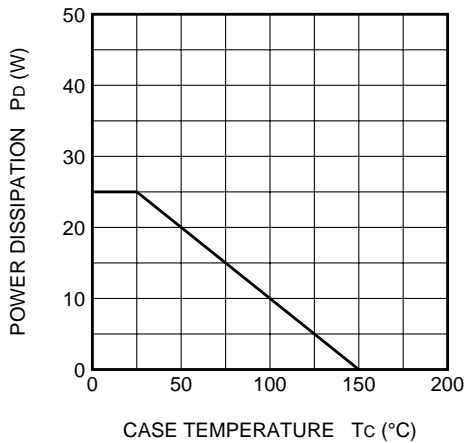
Symbol	Parameter	Conditions	Ratings	Unit
V _{DSS}	Drain-source voltage	V _{GS} = 0V	150	V
V _{GSS}	Gate-source voltage	V _{DS} = 0V	±20	V
I _D	Drain current		10	A
I _{DM}	Drain current (Pulsed)		40	A
I _{DA}	Avalanche drain current (Pulsed)	L = 100μH	10	A
I _S	Source current		10	A
I _{SM}	Source current (Pulsed)		40	A
P _D	Maximum power dissipation		25	W
T _{ch}	Channel temperature		-55 ~ +150	°C
T _{stg}	Storage temperature		-55 ~ +150	°C
V _{iso}	Isolation voltage	AC for 1minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

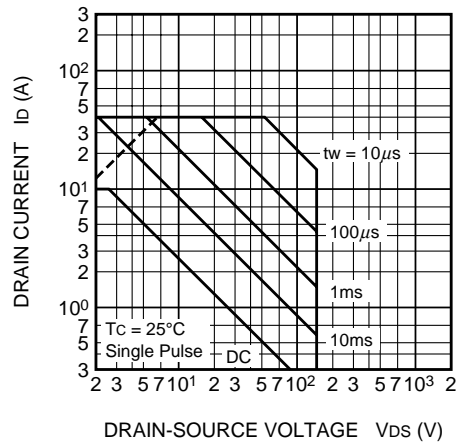
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, Vgs = 0V	150	—	—	V
IgSS	Gate-source leakage current	Vgs = ±20V, Vds = 0V	—	—	±0.1	μA
IbSS	Drain-source leakage current	Vds = 150V, Vgs = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, Vds = 10V	2.0	3.0	4.0	V
rDS (ON)	Drain-source on-state resistance	Id = 5A, Vgs = 10V	—	122	170	mΩ
VDS (ON)	Drain-source on-state voltage	Id = 5A, Vgs = 10V	—	0.61	0.85	V
yfs	Forward transfer admittance	Id = 5A, Vds = 10V	—	12	—	S
Ciss	Input capacitance	Vds = 10V, Vgs = 0V, f = 1MHz	—	1250	—	pF
Coss	Output capacitance		—	175	—	pF
Crss	Reverse transfer capacitance		—	75	—	pF
td (on)	Turn-on delay time	VDD = 80V, Id = 5A, VGS = 10V, RGEN = RGS = 50Ω	—	25	—	ns
tr	Rise time		—	30	—	ns
td (off)	Turn-off delay time		—	60	—	ns
tf	Fall time		—	34	—	ns
VSD	Source-drain voltage	Is = 5A, Vgs = 0V	—	1.0	1.5	V
Rth (ch-c)	Thermal resistance	Channel to case	—	—	5.00	°C/W
trr	Reverse recovery time	Is = 10A, dis/dt = -100A/μs	—	100	—	ns

PERFORMANCE CURVES

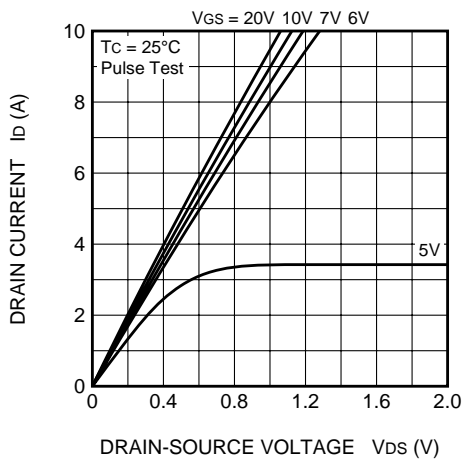
POWER DISSIPATION DERATING CURVE



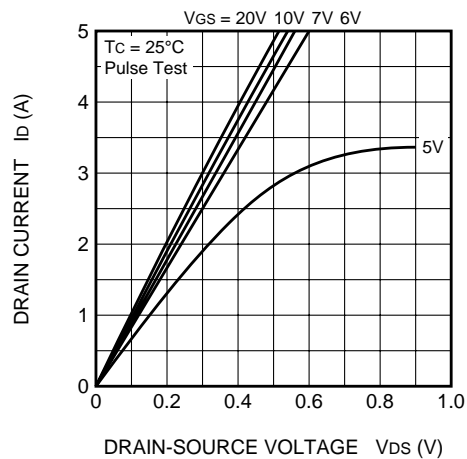
MAXIMUM SAFE OPERATING AREA

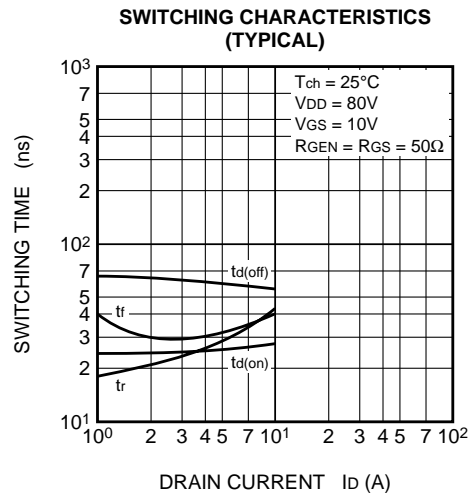
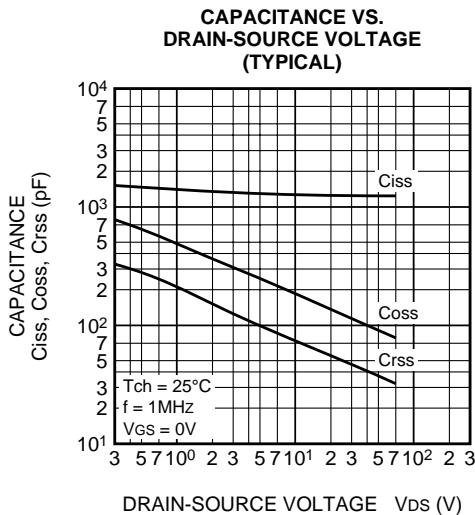
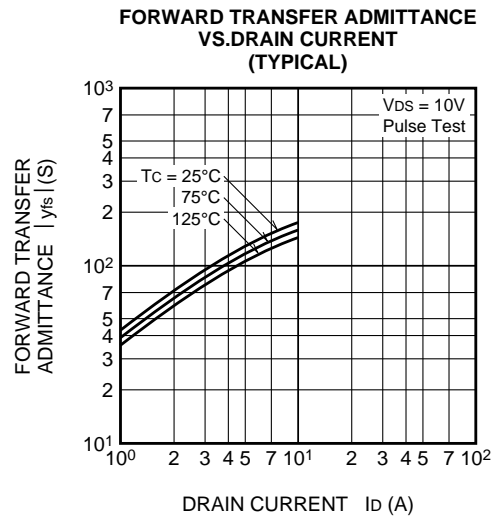
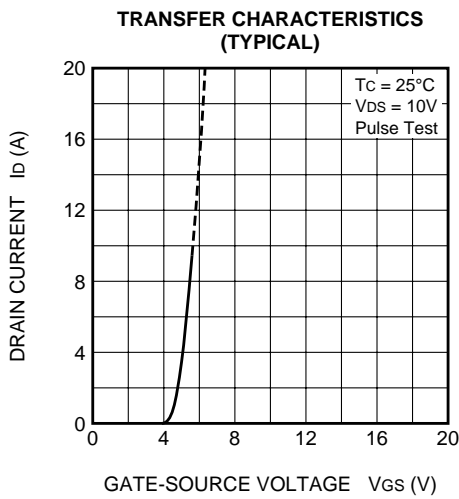
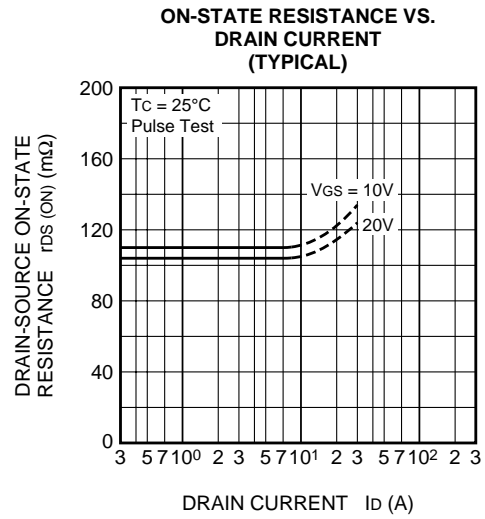
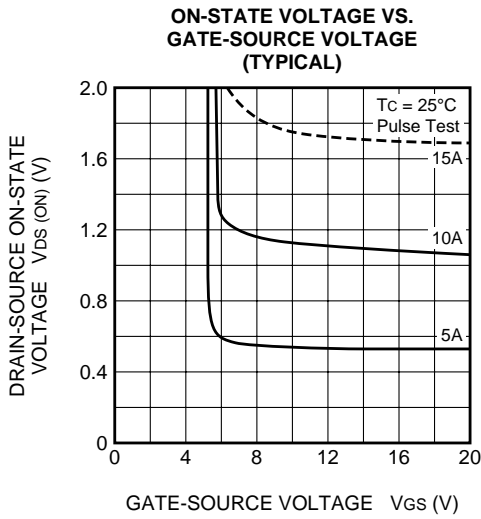


OUTPUT CHARACTERISTICS (TYPICAL)

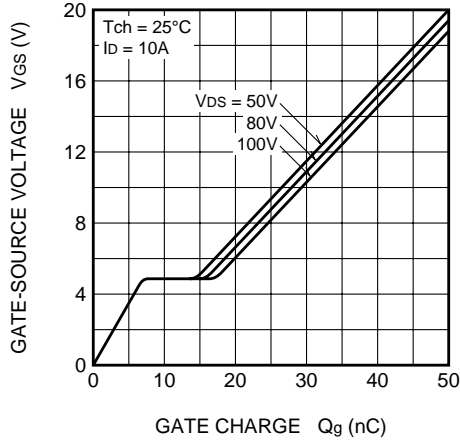


OUTPUT CHARACTERISTICS (TYPICAL)

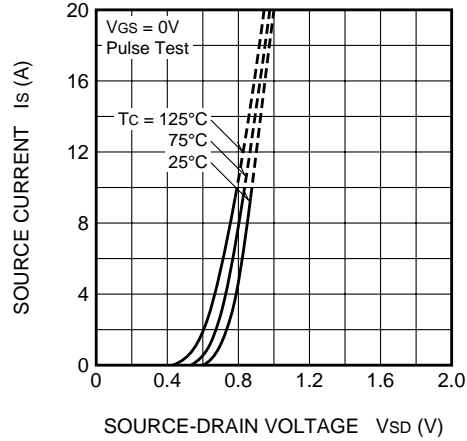




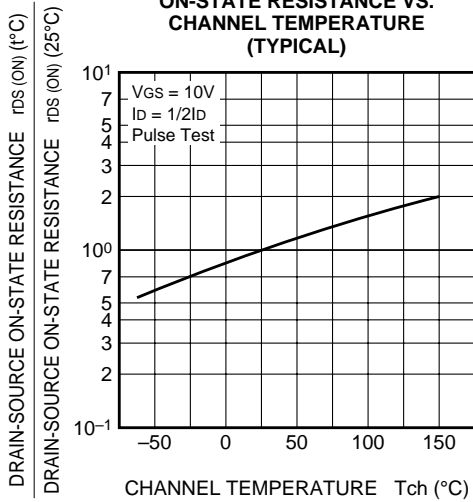
GATE-SOURCE VOLTAGE VS. GATE CHARGE (TYPICAL)



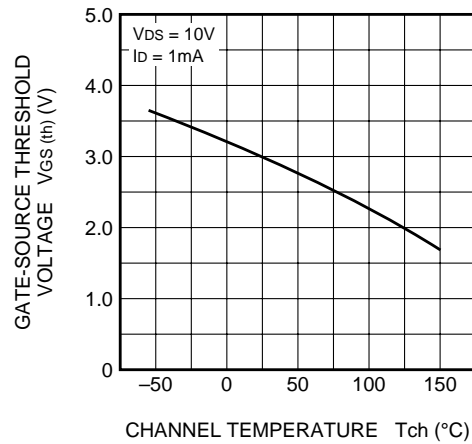
SOURCE-DRAIN DIODE FORWARD CHARACTERISTICS (TYPICAL)



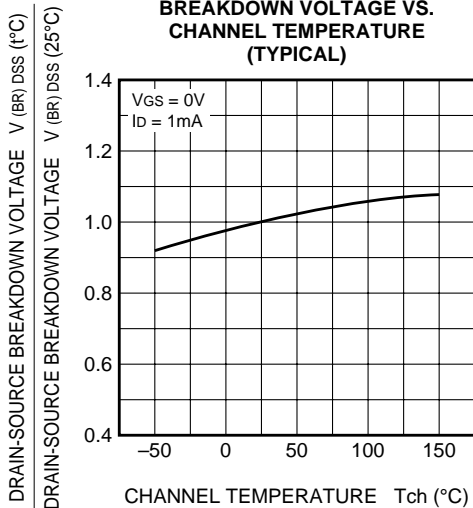
ON-STATE RESISTANCE VS. CHANNEL TEMPERATURE (TYPICAL)



THRESHOLD VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



BREAKDOWN VOLTAGE VS. CHANNEL TEMPERATURE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS

